

SMPS MOSFET

IRF7457PbF

Applications

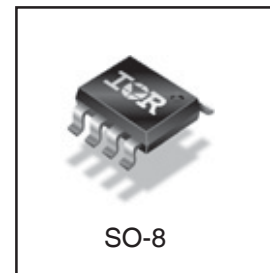
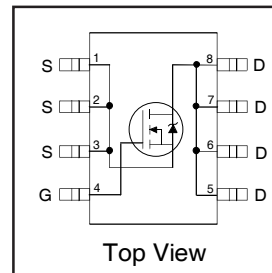
- High Frequency DC-DC Isolated Converters with Synchronous Rectification for Telecom and Industrial use
- High Frequency Buck Converters for Computer Processor Power
- Lead-Free

HEXFET® Power MOSFET

V_{DS}	$R_{DS(on)}$ max	I_D
20V	7.0m Ω	15A

Benefits

- Ultra-Low $R_{DS(on)}$
- Very Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D @ $T_A = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	15	A
I_D @ $T_A = 70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	12	
I_{DM}	Pulsed Drain Current ^①	120	
P_D @ $T_A = 25^\circ\text{C}$	Maximum Power Dissipation ^③	2.5	W
P_D @ $T_A = 70^\circ\text{C}$	Maximum Power Dissipation ^③	1.6	W
	Linear Derating Factor	0.02	W/ $^\circ\text{C}$
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	$^\circ\text{C}$

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	20	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient ^④	—	50	

Notes ^① through ^④ are on page 8
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IRF7457PbF

International
IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.023	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	5.5	7.0	$m\Omega$	$V_{GS} = 10V, I_D = 15A$ ③
		—	8.0	10.5		$V_{GS} = 4.5V, I_D = 12A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 16V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -16V$

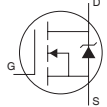
Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

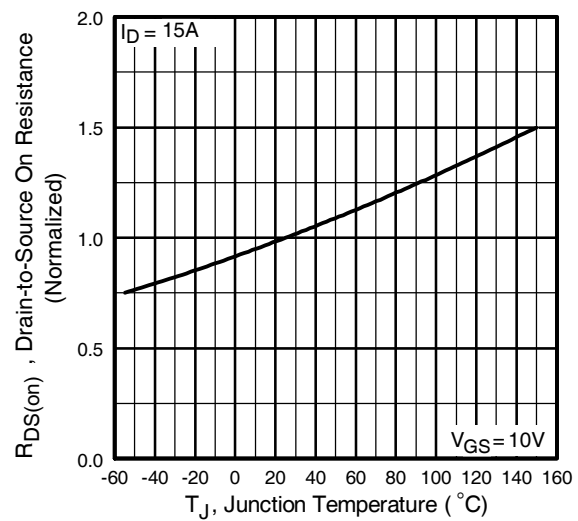
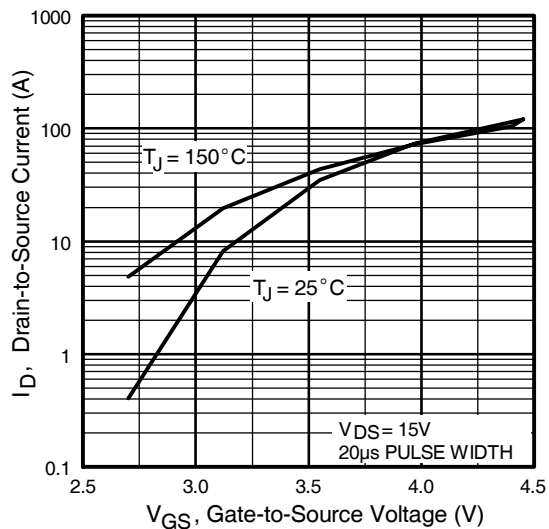
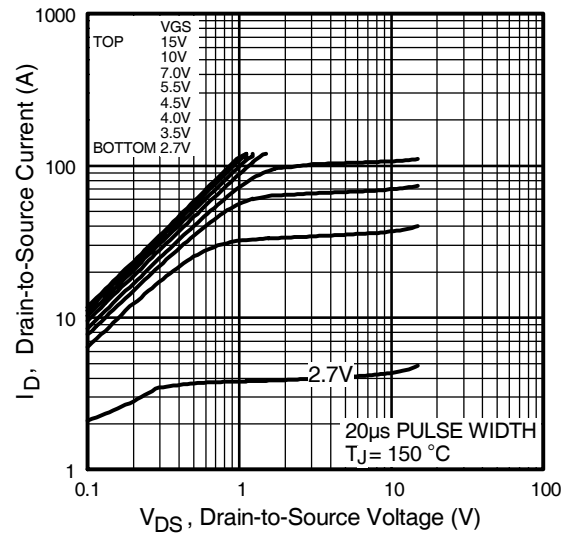
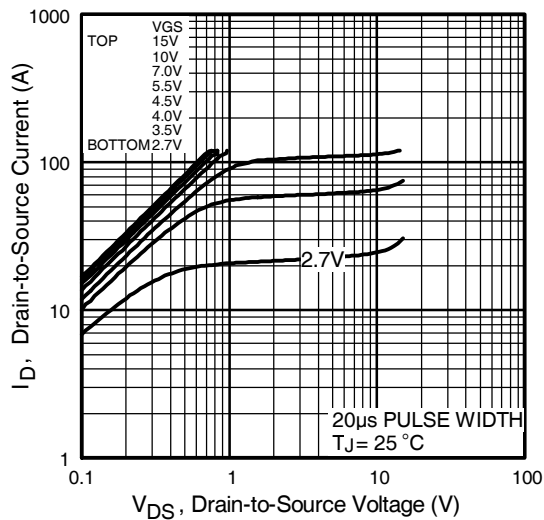
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	30	—	—	S	$V_{DS} = 16V, I_D = 12A$
Q_g	Total Gate Charge	—	28	42	nC	$I_D = 12A$
Q_{gs}	Gate-to-Source Charge	—	11	17		$V_{DS} = 10V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	10	15		$V_{GS} = 4.5V,$ ③
Q_{oss}	Output Gate Charge	—	25	38		$V_{GS} = 0V, V_{DS} = 10V$
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	$V_{DD} = 10V,$
t_r	Rise Time	—	16	—		$I_D = 12A$
$t_{d(off)}$	Turn-Off Delay Time	—	16	—		$R_G = 1.8\Omega$
t_f	Fall Time	—	7.5	—		$V_{GS} = 4.5V$ ③
C_{iss}	Input Capacitance	—	3100	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1600	—		$V_{DS} = 10V$
C_{rss}	Reverse Transfer Capacitance	—	270	—		$f = 1.0\text{MHz}$

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	265	mJ
I_{AR}	Avalanche Current①	—	15	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	120		
V_{SD}	Diode Forward Voltage	—	0.8	1.3	V	$T_J = 25^\circ\text{C}, I_S = 12A, V_{GS} = 0V$ ③
		—	0.67	—		$T_J = 125^\circ\text{C}, I_S = 12A, V_{GS} = 0V$
t_{rr}	Reverse Recovery Time	—	50	75	ns	$T_J = 25^\circ\text{C}, I_F = 12A, V_R = 15V$
Q_{rr}	Reverse Recovery Charge	—	70	105	nC	$di/dt = 100A/\mu s$ ③
t_{rr}	Reverse Recovery Time	—	50	75	ns	$T_J = 125^\circ\text{C}, I_F = 12A, V_R = 15V$
Q_{rr}	Reverse Recovery Charge	—	74	110	nC	$di/dt = 100A/\mu s$ ③



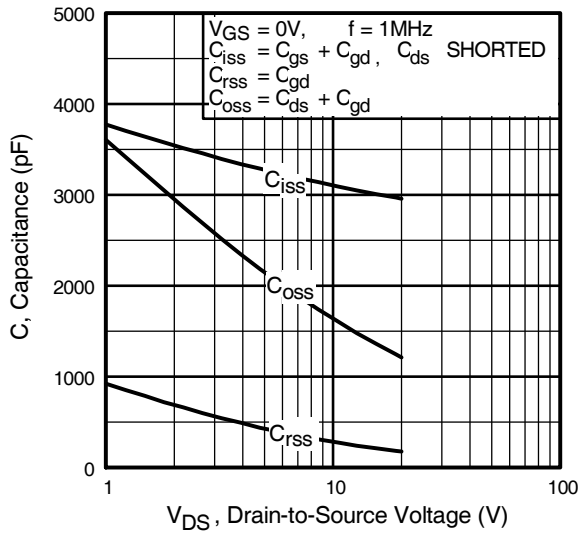


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

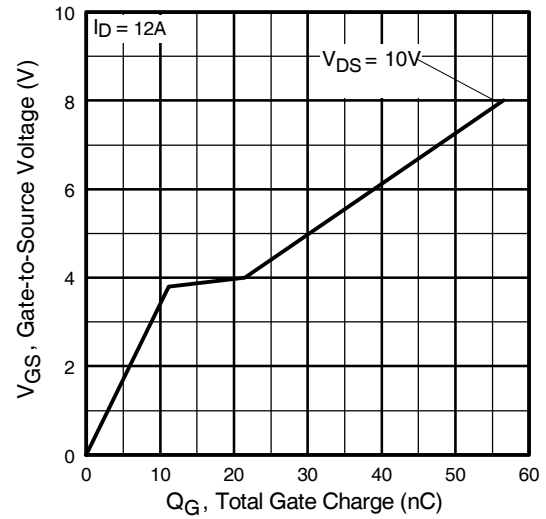


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

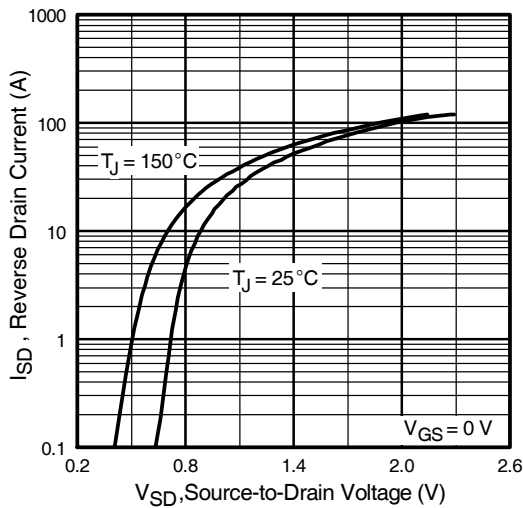


Fig 7. Typical Source-Drain Diode Forward Voltage

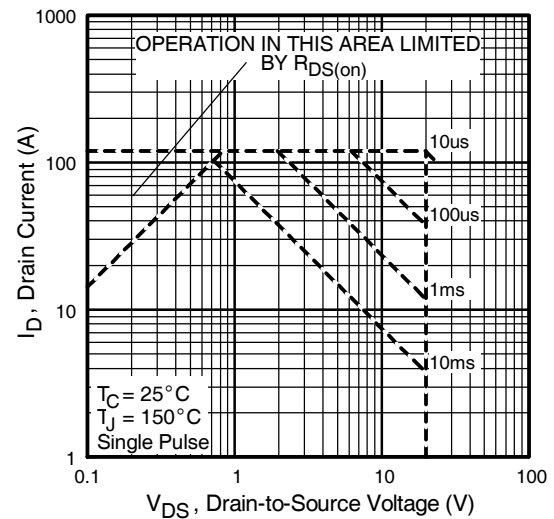


Fig 8. Maximum Safe Operating Area

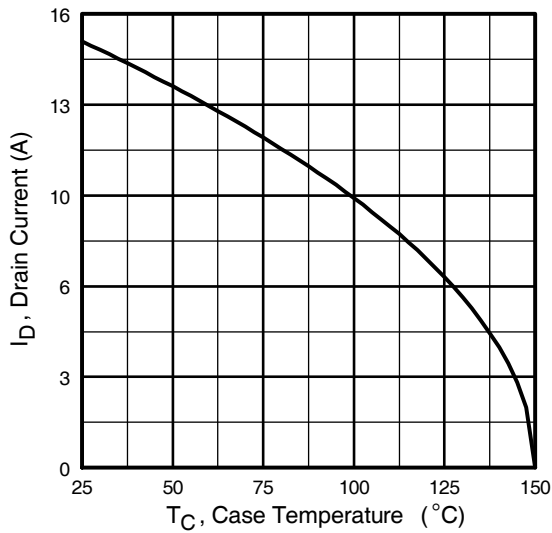


Fig 9. Maximum Drain Current Vs. Case Temperature

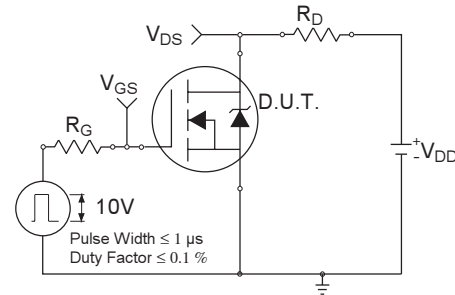


Fig 10a. Switching Time Test Circuit

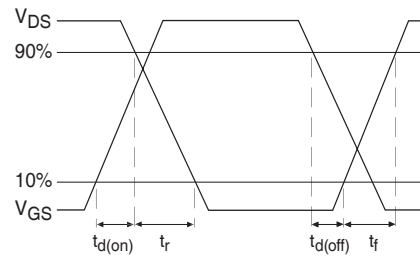


Fig 10b. Switching Time Waveforms

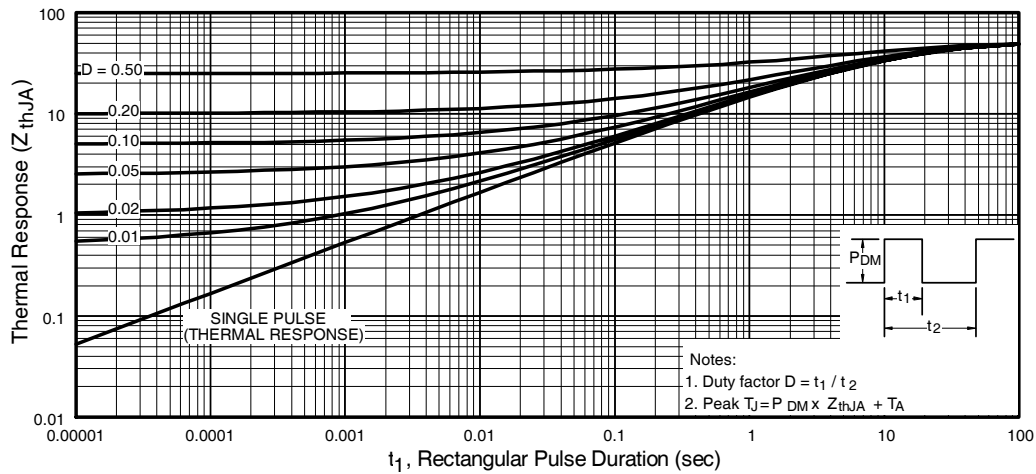


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

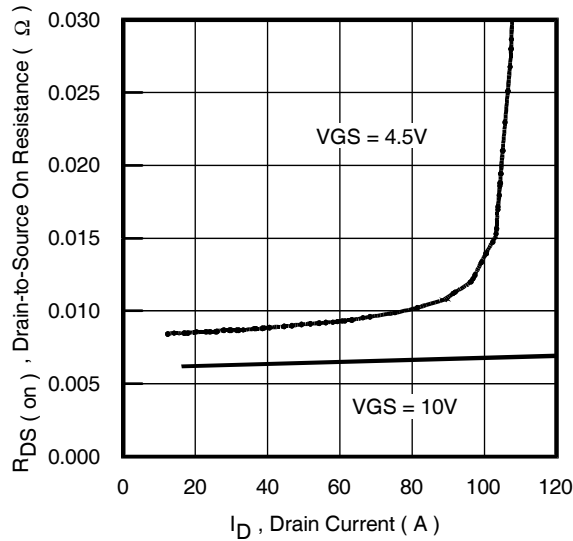


Fig 12. On-Resistance Vs. Drain Current

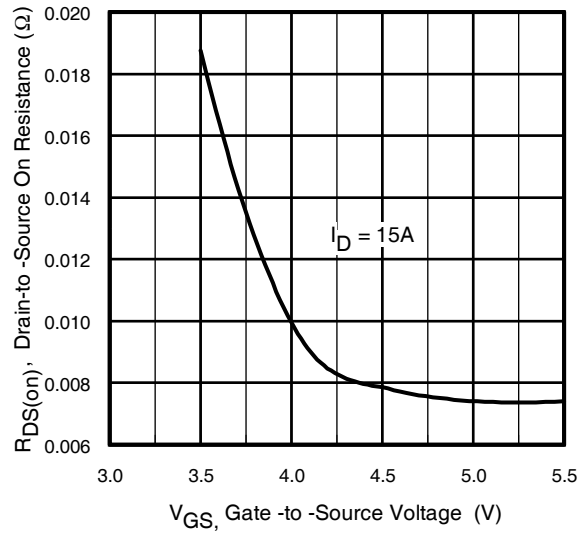


Fig 14. On-Resistance Vs. Gate Voltage

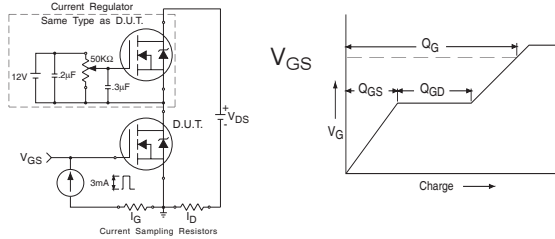


Fig 13a&b. Basic Gate Charge Test Circuit and Waveform

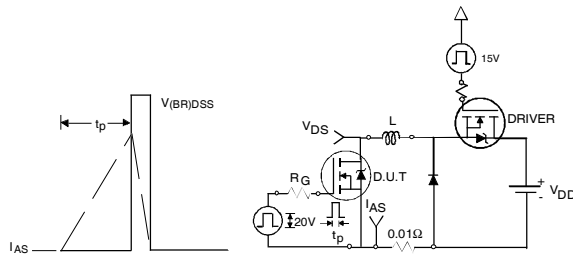


Fig 14a&b. Unclamped Inductive Test circuit and Waveforms

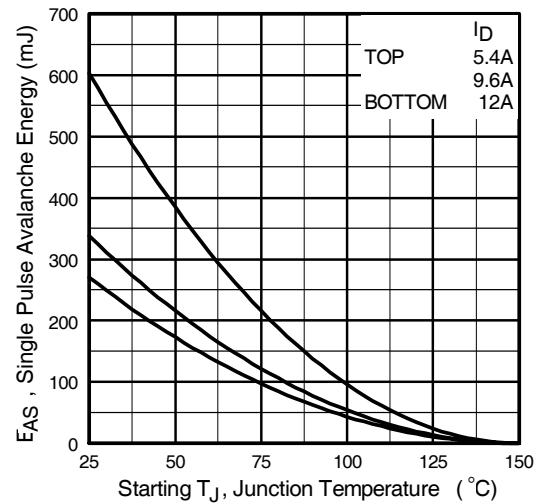
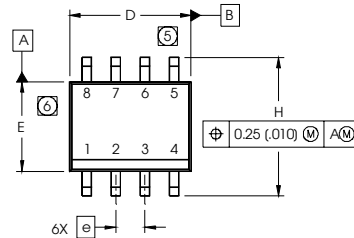


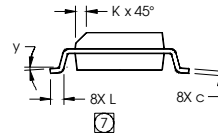
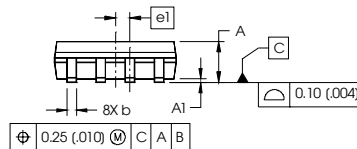
Fig 14c. Maximum Avalanche Energy Vs. Drain Current

SO-8 Package Outline

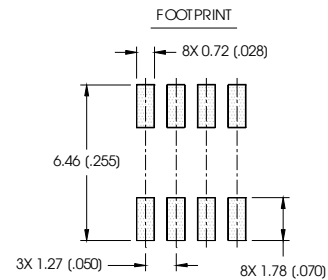
Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

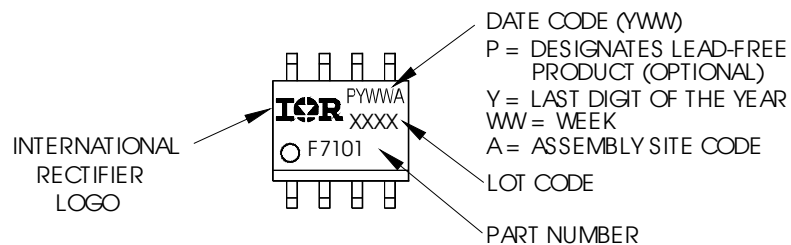


- NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: MILLIMETER
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
 5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (0.006).
 6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (0.010).
 7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



SO-8 Part Marking Information (Lead-Free)

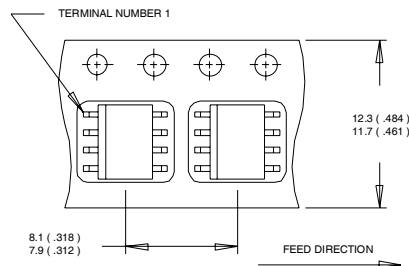
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



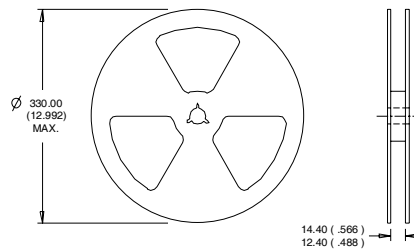
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SO-8 Tape and Reel



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 3.7\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 12\text{A}$.
- ③ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board, $t < 10\text{ sec}$

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualification Standards can be found on IR's Web site.

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IR Rectifier

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